

# XN02501 (XN2501)

Silicon NPN epitaxial planar type

For general amplification

## ■ Features

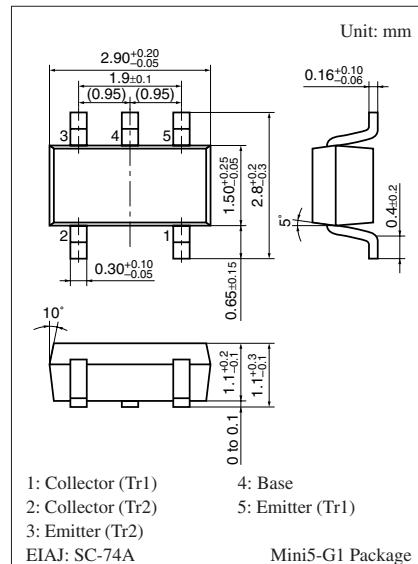
- Two elements incorporated into one package  
(Base-coupled transistors)
- Reduction of the mounting area and assembly cost by one half

## ■ Basic Part Number

- 2SD0601A (2SD601A) × 2

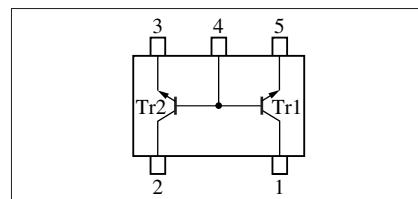
## ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	60	V
Collector-emitter voltage (Base open)	$V_{CEO}$	50	V
Emitter-base voltage (Collector open)	$V_{EBO}$	7	V
Collector current	$I_C$	100	mA
Peak collector current	$I_{CP}$	200	mA
Total power dissipation	$P_T$	300	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$



Marking Symbol: 5W

## Internal Connection



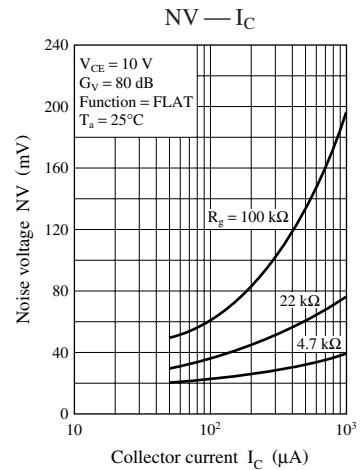
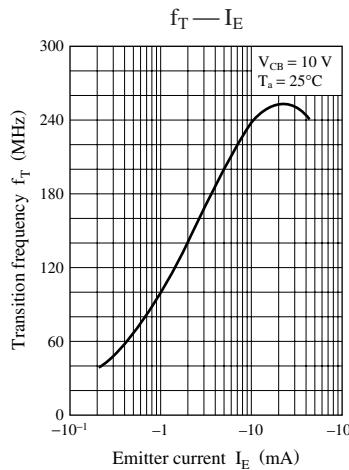
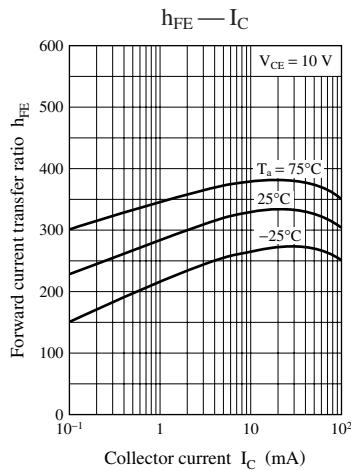
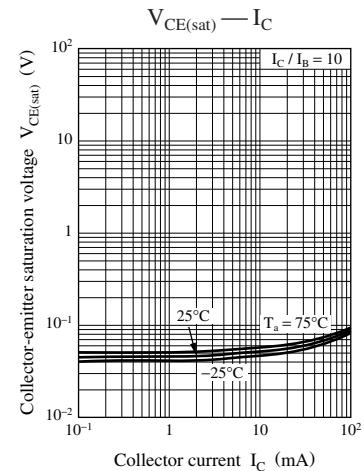
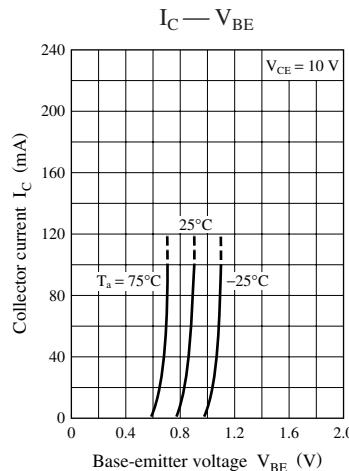
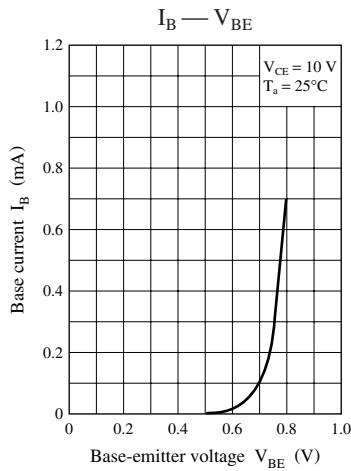
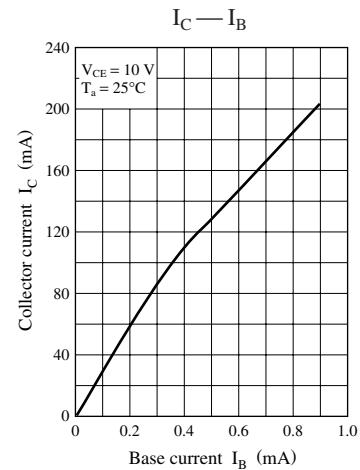
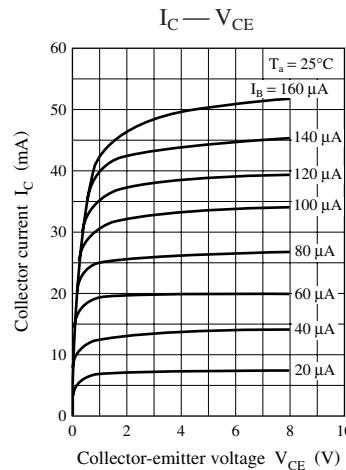
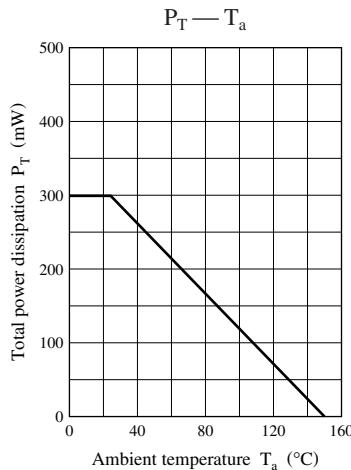
## ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 10 \mu\text{A}, I_E = 0$	60			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 2 \text{ mA}, I_B = 0$	50			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 10 \mu\text{A}, I_C = 0$	7			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 20 \text{ V}, I_E = 0$			0.1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 10 \text{ V}, I_B = 0$			100	$\mu\text{A}$
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 10 \text{ V}, I_C = 2 \text{ mA}$	160		460	—
$h_{FE}$ ratio *	$h_{FE}(\text{Small/Large})$	$V_{CE} = 10 \text{ V}, I_C = 2 \text{ mA}$	0.50	0.99		—
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$		0.1	0.3	V
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		150		MHz
Collector output capacitance (Common base, input open circuited)	$C_{ob}$	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		3.5		pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*: Ratio between 2 elements

Note) The part number in the parenthesis shows conventional part number.



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